PATENT
Attorney Docket No. 03-0730
Express Mail No. EU790295322US

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Mohammad R. Mirabedini Valeriy Sukharev	)	Group Art Unit: Not yet assigned
Serial No. Not yet assigned	)	Examiner: Not yet assigned
Filed: Concurrently	)	
For: Apparatus and Method of Manufacture for Integrated Circuit and CMOS Device Including Epitaxially Grown Dielectric on Silicon Carbide	)	

INFORMATION DISCLOSURE STATEMENT

Honorable Commissioner of Patents and Trademarks
Washington, D.C. 20231

Sir:

The Examiner may wish to consider the following references during the examination of the above-identified application:

NON PATENT LITERATURE DOCUMENTS

1 Nobuyuki Sugii, Digh Hisamoto, Katsuyoshi Washio, Natsuki Yokoyama, and Shin'ichiro Kimura, "Enhanced Performance of Strained-Si MOSFETs on CMP SiGe Virtual Substrate," IEEE, 2001, 0-7803-7052-X/01, p. 1-4.

2 Paul Comita, AnnaLena Thilderkvist, and Arkadii V. Samoilov, "Applied Materials FEOL Seminar 2002," October 29, 2002, p. 1-37.

3 K. Rim, S. Koester, M. Hargrove, J. Chu, P. M. Mooney, J. Ott, T. Kanarsky, P. Ronsheim, M.Ieong, A. Grill, and H.-S. P. Wong, "Strained Si NMOSFETs for High Performance CMOS Technology," IEEE 2001 Symposium on VLSI Technology Digest of Technical Papers, 2001, p. 59 (1-2).

4 Yee-Chia Yeo, Qiang Lu, Chenming Hu, Tsu-Jae King, T. Kawashima, M. Oishi, S. Mashiro, and J. Sakai, "Enhanced performance in sub-100 nm CMOSFETs using strained epitaxial silicon-germanium", IEEE International Electron Device Meeting Technical Digest, pp. 753-756, San Francisco, CA, Dec. 2000, www.eecs.berkeley.edu/IPRO/Summary/01abstracts/ycyeo.1.html, p. 1-4.

5 R.E. Stallcup, A.F. Aviles, and J.M. Perez, "Atomic Resolution Ultrahigh Vacuum Scanning Tunneling Microscopy of Epitaxial Diamond (100) Films," Appl. Phys. Lett. 66 (18), American Institute of Physics, 1 May 1995, p. 2331-2333.

6 Akira Yamada, Tatsuro Watahiki, Shuhei Yagi, Katsuya Abe, and Makoto Konagai, "Epitaxial Growth of Strained Si_{1-x} C_x on Si and Its Application to MOSFET," International Symposium on Quantum Effect Electronics, 2002.

Attached is a completed Form PTO-1449 for the Examiner's convenience in citing these references. Copies of the above identified references are also enclosed.

Signed at Highlands Ranch, Colorado this 10th day of September, 2003.

Respectfully submitted,

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PTO/SB/08B (02-03)
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Substitute for form 1449/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet 1 of 1

Complete if Known	
Application Number	Not Yet Assigned
Filing Date	Concurrently
First Named Inventor	Mohammad R. Mirabedini
Art Unit	Not Yet Assigned
Examiner Name	Not Yet Assigned
Attorney Docket Number	03-0730

OTHER PRIOR ART–NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
	1	Nobuyuki Sugii, Digh Hisamoto, Katsuyoshi Washio, Natsuki Yokoyama, and Shin'ichiro Kimura, "Enhanced Performance of Strained-Si MOSFETs on CMP SiGe Virtual Substrate," IEEE, 2001, 0-7803-7052-X/01, p. 1-4.	
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	5	R.E. Stallcup, A.F. Aviles, and J.M. Perez, "Atomic Resolution Ultrahigh Vacuum Scanning Tunneling Microscopy of Epitaxial Diamond (100) Films," Appl. Phys. Lett. 66 (18), American Institute of Physics, 1 May 1995, p. 2331-2333.	
	6	Akira Yamada, Tatsuro Watahiki, Shuhei Yagi, Katsuya Abe, and Makoto Konagai, "Epitaxial Growth of Strained $Si_{1-x}C_x$ on Si and Its Application to MOSFET," International Symposium on Quantum Effect Electronics, 2002.	

Examiner Signature		Date Considered	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

[1] Applicant's unique citation designation number (optional). [2] Applicant is to place a check mark here if English language Translation is attached.